



# BU808DFI

## HIGH VOLTAGE FAST-SWITCHING NPN POWER DARLINGTON

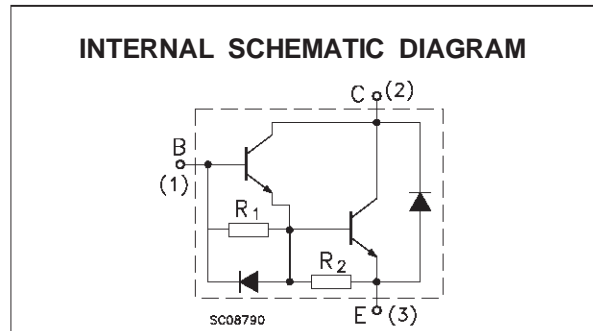
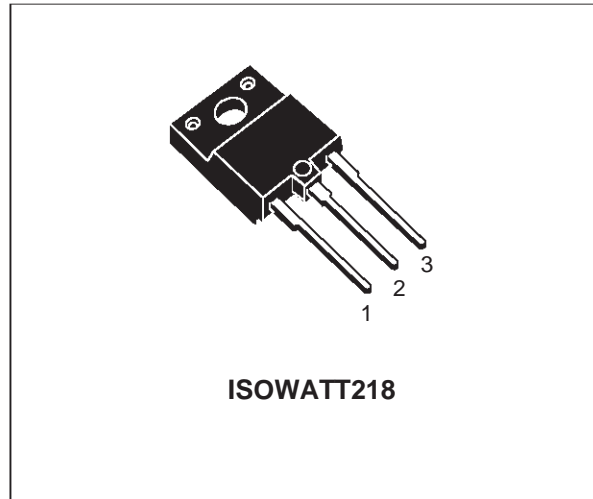
- STMicroelectronics PREFERRED SALESTYPE
- NPN MONOLITHIC DARLINGTON WITH INTEGRATED FREE-WHEELING DIODE
- HIGH VOLTAGE CAPABILITY ( $> 1400\text{ V}$ )
- HIGH DC CURRENT GAIN ( TYP. 150 )
- U.L. RECOGNISED ISOWATT218 PACKAGE (U.L. FILE # E81734 (N))
- LOW BASE-DRIVE REQUIREMENTS
- DEDICATED APPLICATION NOTE AN1184

### APPLICATIONS

- COST EFFECTIVE SOLUTION FOR HORIZONTAL DEFLECTION IN LOW END TV UP TO 21 INCHES.

### DESCRIPTION

The BU808DFI is a NPN transistor in monolithic Darlington configuration. It is manufactured using Multi-epitaxial Mesa technology for cost-effective high performance.



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CB0}$	Collector-Base Voltage ( $I_E = 0$ )	1400	V
$V_{CE0}$	Collector-Emitter Voltage ( $I_B = 0$ )	700	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	5	V
$I_C$	Collector Current	8	A
$I_{CM}$	Collector Peak Current ( $t_p < 5\text{ ms}$ )	10	A
$I_B$	Base Current	3	A
$I_{BM}$	Base Peak Current ( $t_p < 5\text{ ms}$ )	6	A
$P_{tot}$	Total Dissipation at $T_c = 25\text{ }^\circ\text{C}$	52	W
$T_{stg}$	Storage Temperature	-65 to 150	$^\circ\text{C}$
$T_j$	Max. Operating Junction Temperature	150	$^\circ\text{C}$

# BU808DFI

## THERMAL DATA

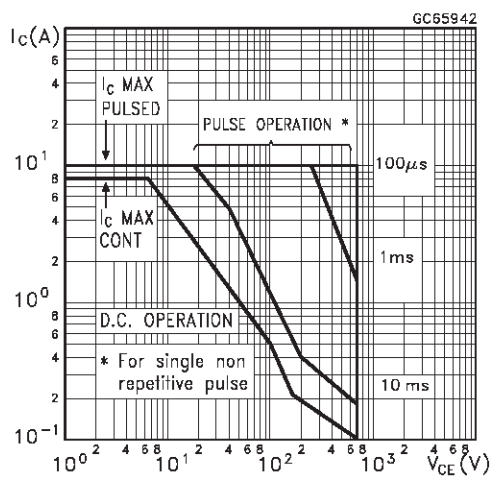
$R_{thj-case}$	Thermal Resistance Junction-case	Max	2.4	$^{\circ}C/W$
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## ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}C$ unless otherwise specified)

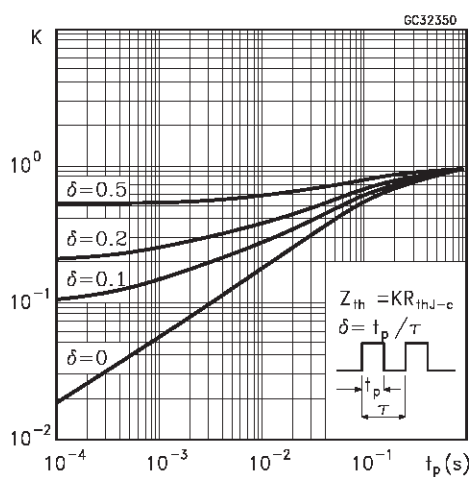
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CES}$	Collector Cut-off Current ( $V_{BE} = 0$ )	$V_{CE} = 1400 V$			400	$\mu A$
$I_{EBO}$	Emitter Cut-off Current ( $I_C = 0$ )	$V_{EB} = 5 V$			100	mA
$V_{CE(sat)*}$	Collector-Emitter Saturation Voltage	$I_C = 5 A$ $I_B = 0.5 A$			1.6	V
$V_{BE(sat)*}$	Base-Emitter Saturation Voltage	$I_C = 5 A$ $I_B = 0.5 A$			2.1	V
$h_{FE*}$	DC Current Gain	$I_C = 5 A$ $V_{CE} = 5 V$ $I_C = 5 A$ $V_{CE} = 5 V$ $T_j = 100^{\circ}C$	60 20		230	
$t_s$ $t_f$	INDUCTIVE LOAD Storage Time Fall Time	$V_{CC} = 150 V$ $I_C = 5 A$ $I_{B1} = 0.5 A$ $V_{BEoff} = -5 V$			3 0.8	$\mu s$ $\mu s$
$t_s$ $t_f$	INDUCTIVE LOAD Storage Time Fall Time	$V_{CC} = 150 V$ $I_C = 5 A$ $I_{B1} = 0.5 A$ $V_{BEoff} = -5 V$ $T_j = 100^{\circ}C$		2 0.8		$\mu s$ $\mu s$
$V_F$	Diode Forward Voltage	$I_F = 5 A$			3	V

\* Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %

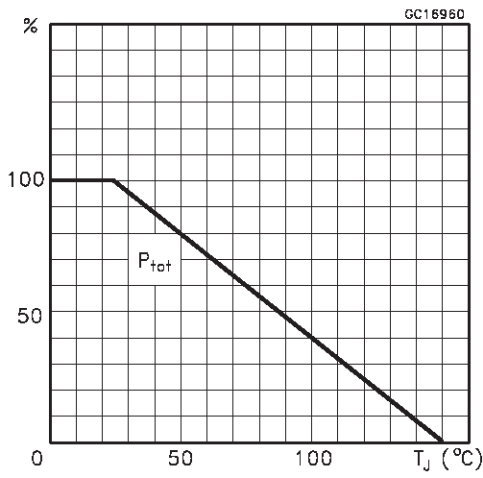
### Safe Operating Area



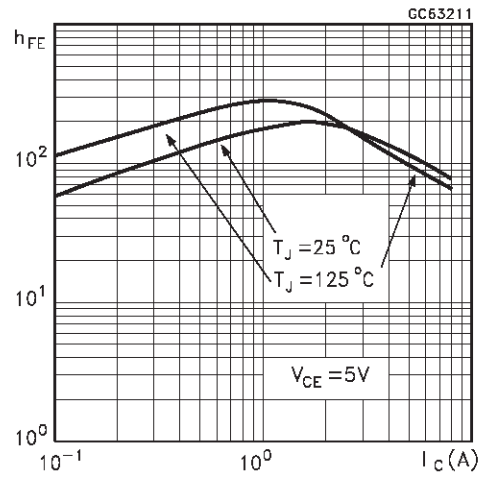
### Thermal Impedance



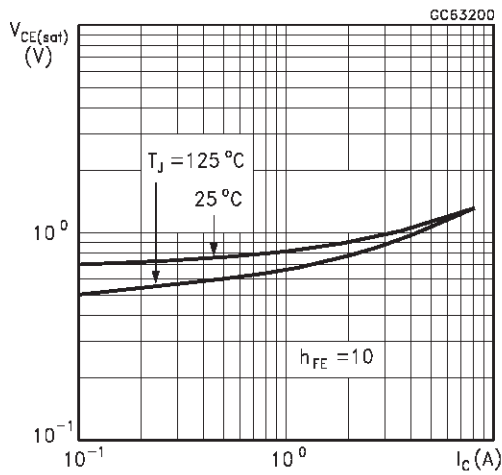
Derating Curve



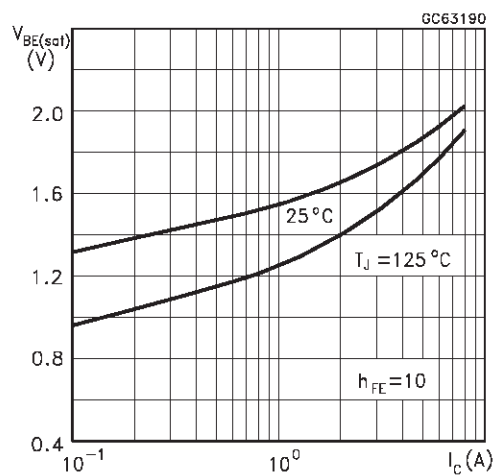
DC Current Gain



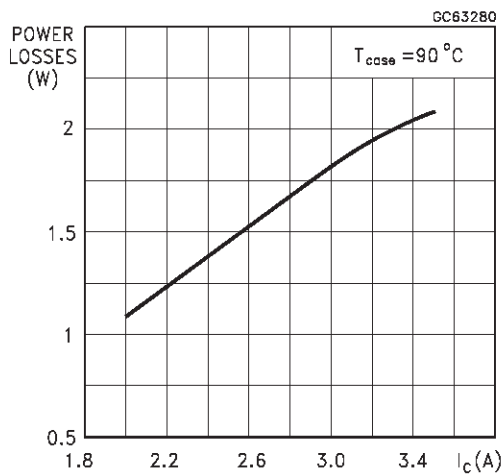
Collector Emitter Saturation Voltage



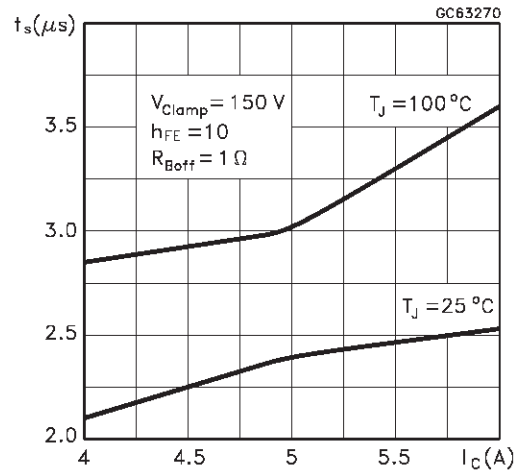
Base Emitter Saturation Voltage



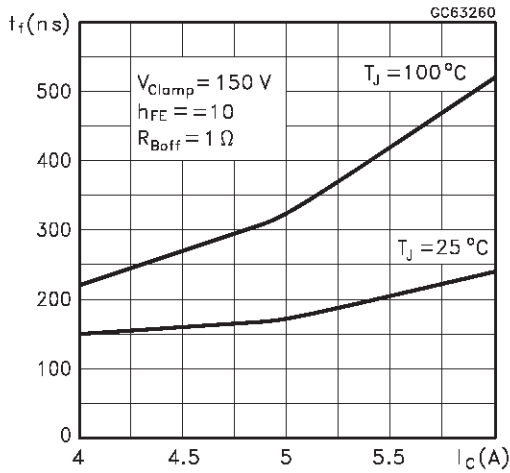
Power Losses at 16 KHz



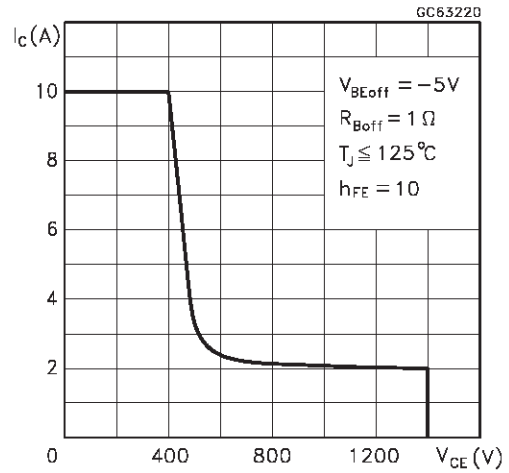
Switching Time Inductive Load at 16KHz



Switching Time Inductive Load at 16KHZ



Reverse Biased SOA



**BASE DRIVE INFORMATION**

In order to saturate the power switch and reduce conduction losses, adequate direct base current  $I_{B1}$  has to be provided for the lowest gain  $h_{FE}$  at  $100\ ^\circ\text{C}$  (line scan phase). On the other hand, negative base current  $I_{B2}$  must be provided to turn off the power transistor (retrace phase).

Most of the dissipation, in the deflection application, occurs at switch-off. Therefore it is essential to determine the value of  $I_{B2}$  which minimizes power losses, fall time  $t_f$  and, consequently,  $T_J$ . A new set of curves have been defined to give total power losses,  $t_s$  and  $t_f$  as a function of  $I_{B2}$  at both 16 KHz scanning frequencies for choosing the optimum negative

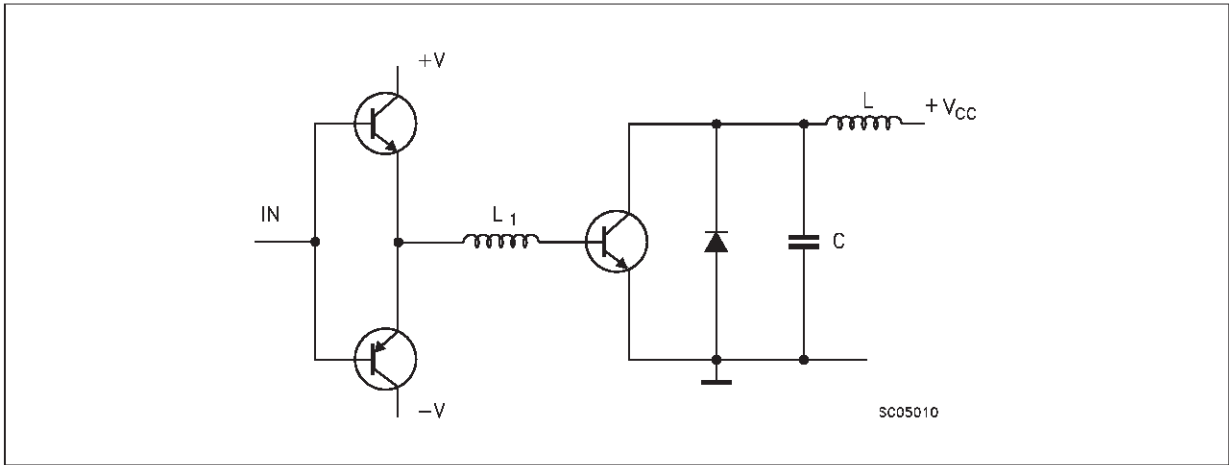
drive. The test circuit is illustrated in figure 1. Inductance  $L_1$  serves to control the slope of the negative base current  $I_{B2}$  to recombine the excess carrier in the collector when base current is still present, this would avoid any tailing phenomenon in the collector current.

The values of  $L$  and  $C$  are calculated from the following equations:

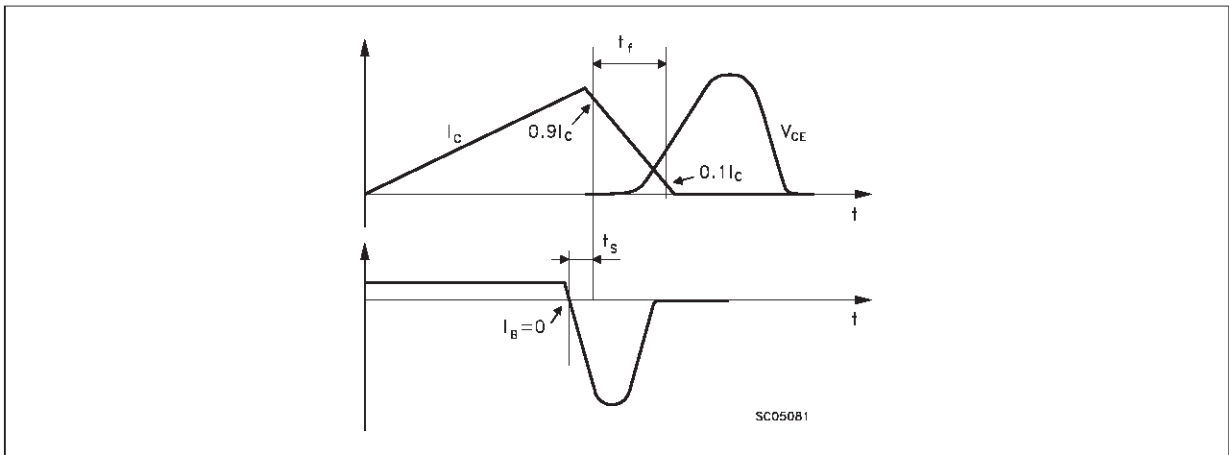
$$\frac{1}{2} L (I_C)^2 = \frac{1}{2} C (V_{CEfly})^2 \quad \omega = 2\pi f = \frac{1}{\sqrt{LC}}$$

Where  $I_C$ = operating collector current,  $V_{CEfly}$ = flyback voltage,  $f$ = frequency of oscillation during retrace.

**Figure 1: Inductive Load Switching Test Circuits.**

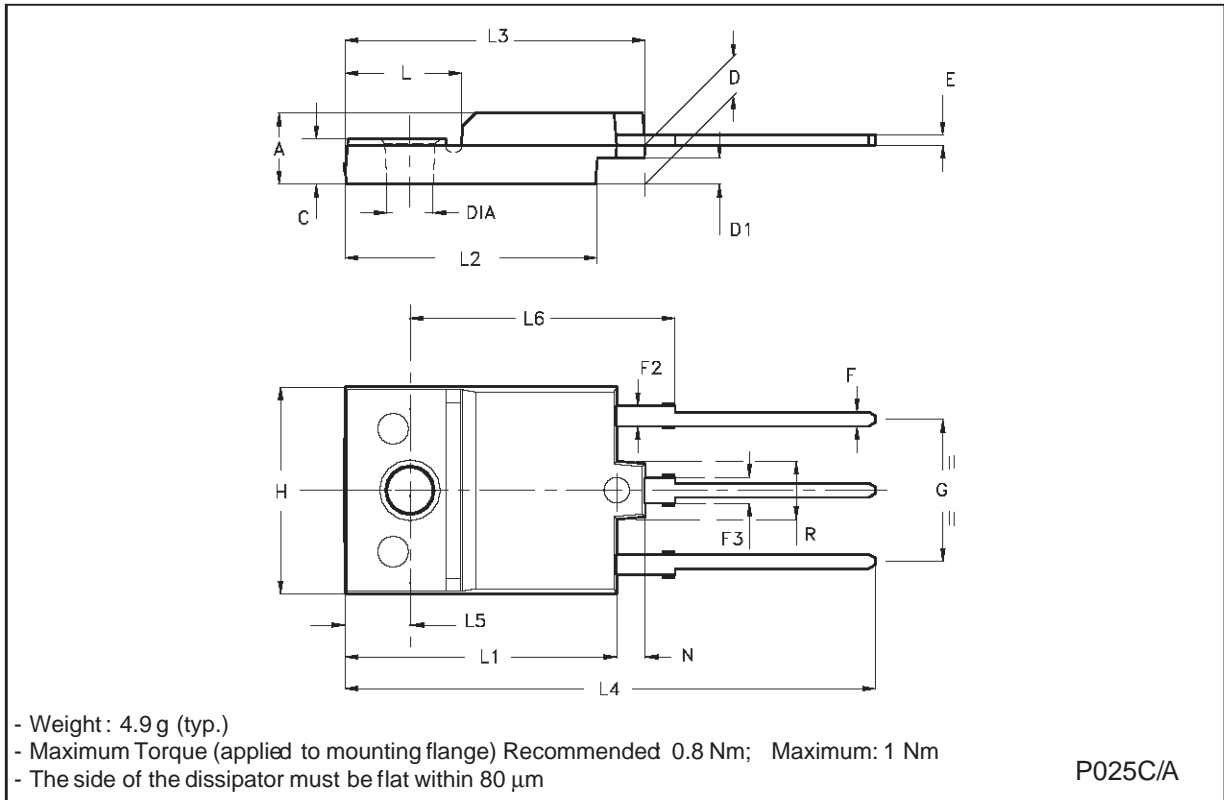


**Figure 2: Switching Waveforms in a Deflection Circuit**



**ISOWATT218 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.35		5.65	0.211		0.222
C	3.30		3.80	0.130		0.150
D	2.90		3.10	0.114		0.122
D1	1.88		2.08	0.074		0.082
E	0.75		0.95	0.030		0.037
F	1.05		1.25	0.041		0.049
F2	1.50		1.70	0.059		0.067
F3	1.90		2.10	0.075		0.083
G	10.80		11.20	0.425		0.441
H	15.80		16.20	0.622		0.638
L		9			0.354	
L1	20.80		21.20	0.819		0.835
L2	19.10		19.90	0.752		0.783
L3	22.80		23.60	0.898		0.929
L4	40.50		42.50	1.594		1.673
L5	4.85		5.25	0.191		0.207
L6	20.25		20.75	0.797		0.817
N	2.1		2.3	0.083		0.091
R		4.6			0.181	
DIA	3.5		3.7	0.138		0.146



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